

Fig. 1 is a cross-sectional view of a semiconductor device. It shows a substrate 11 with a thin layer 22 on its top surface. A patterned layer 27 is formed on top of layer 22, and vertical structures 28 are formed on top of layer 27.

FIG. 3

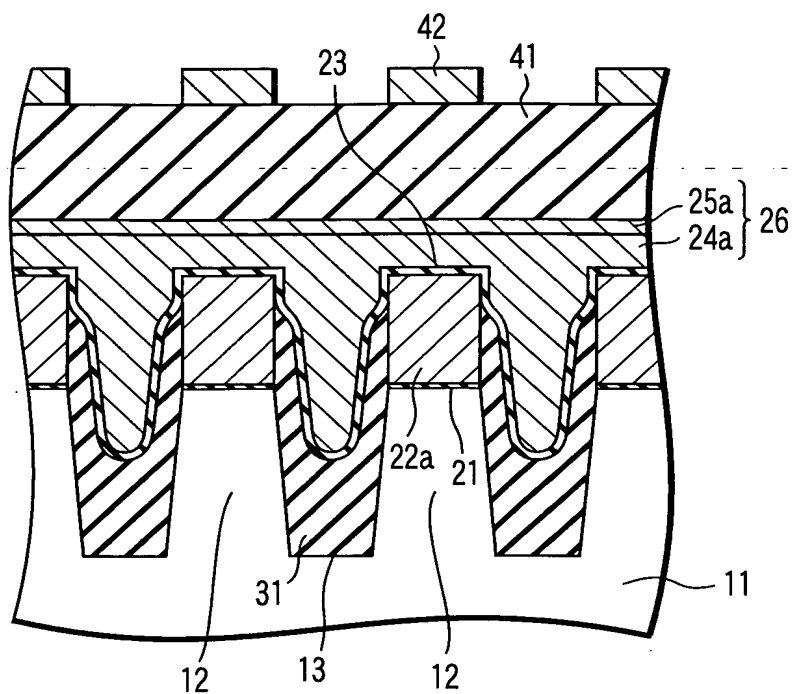


FIG. 2A

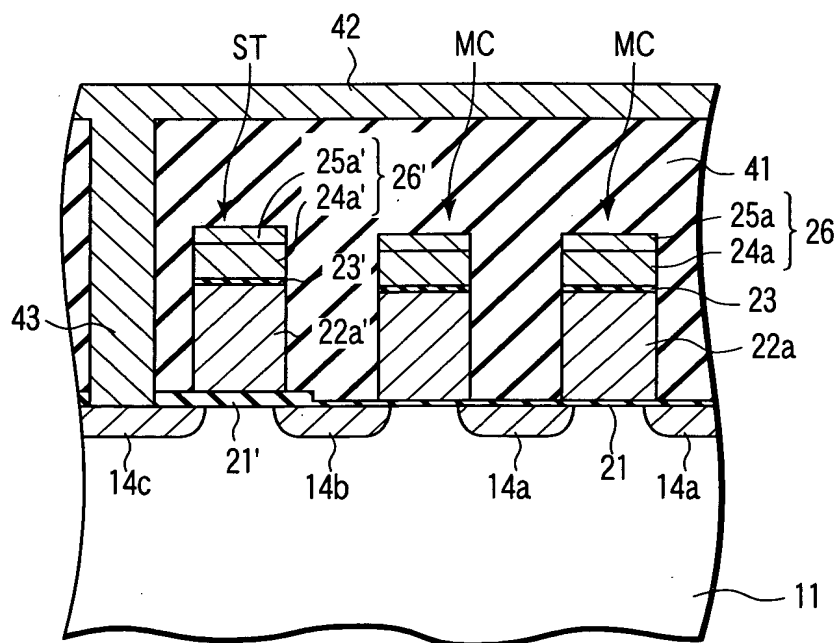


FIG. 2B

FIG. 4

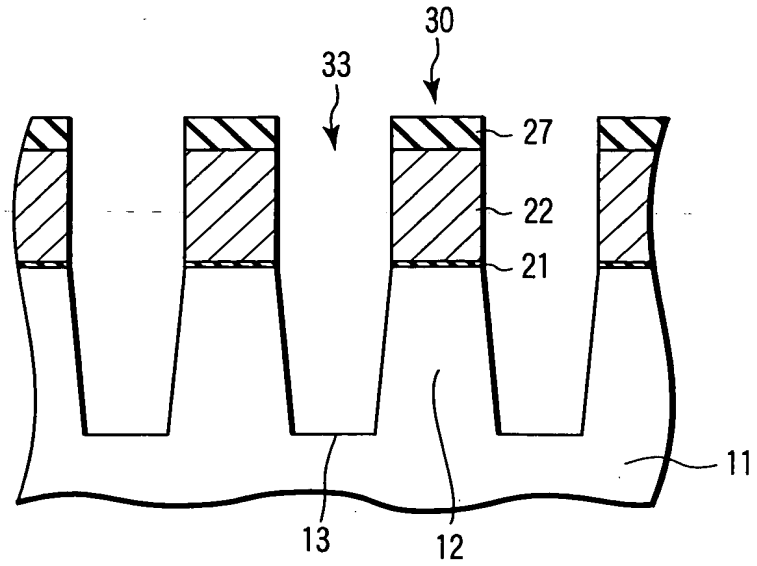


FIG. 5

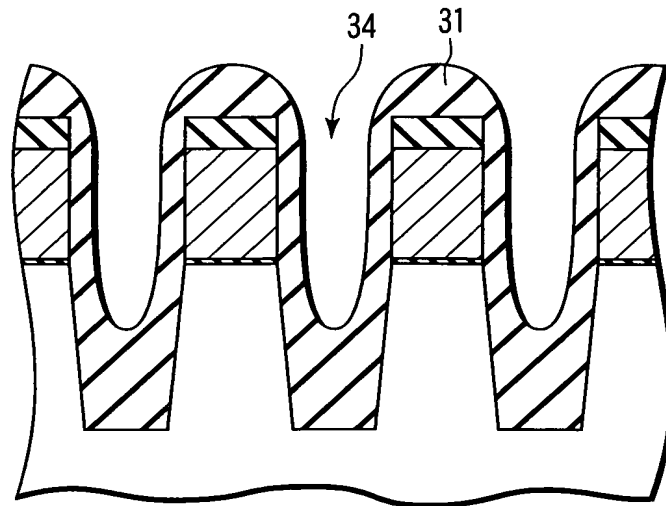


FIG. 6

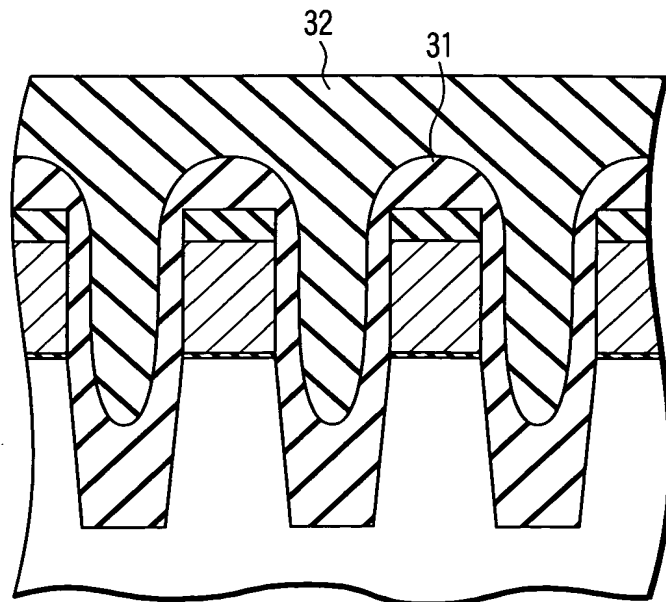


FIG. 7

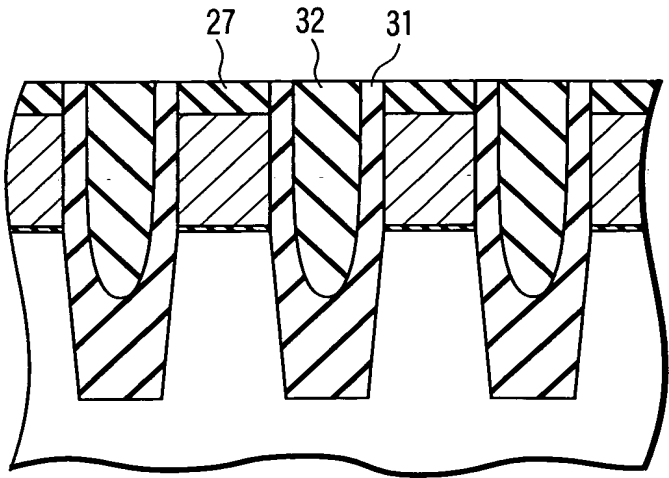


FIG. 8

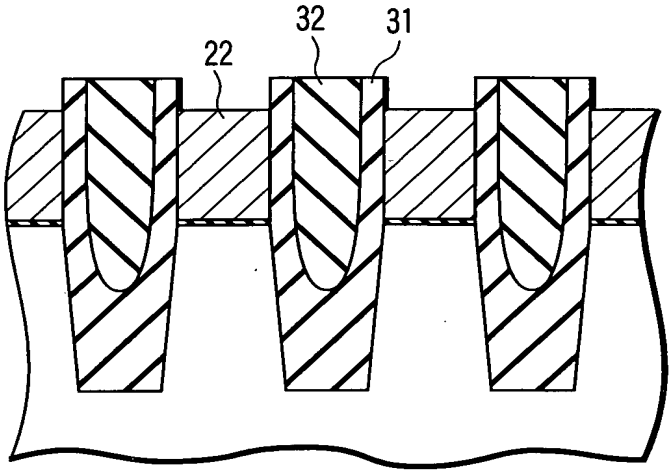
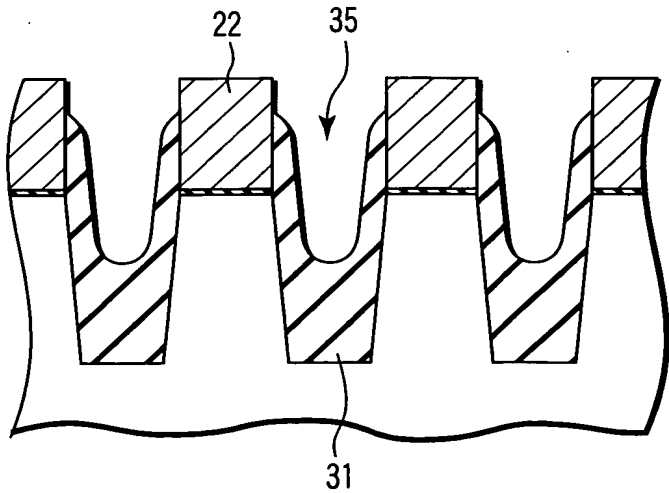


FIG. 9



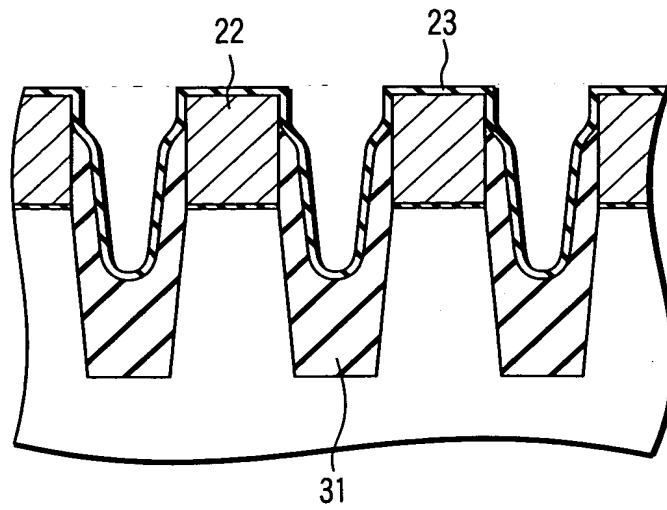


FIG. 10

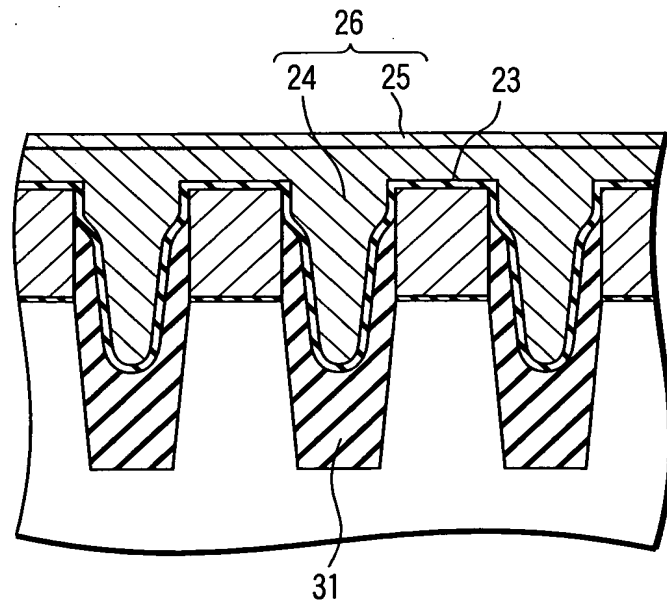


FIG. 11

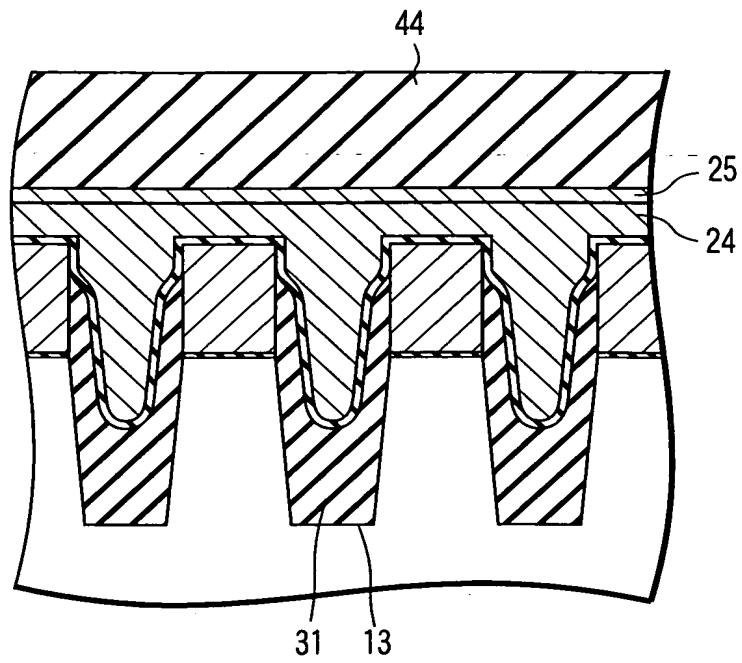


FIG. 12A

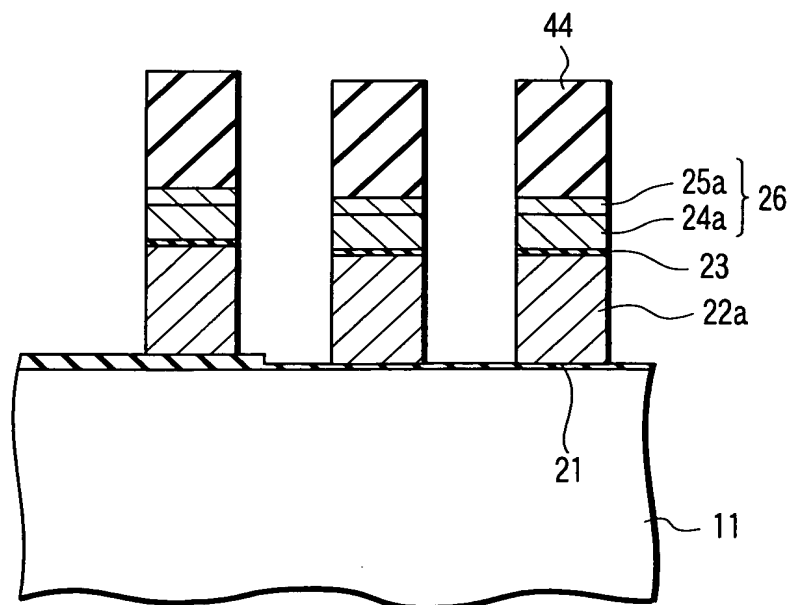


FIG. 12B

FIG. 13
PRIOR ART

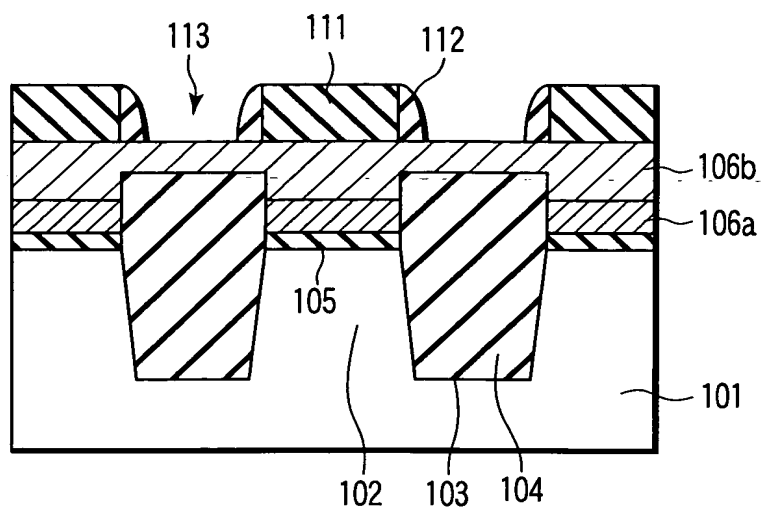


FIG. 14
PRIOR ART

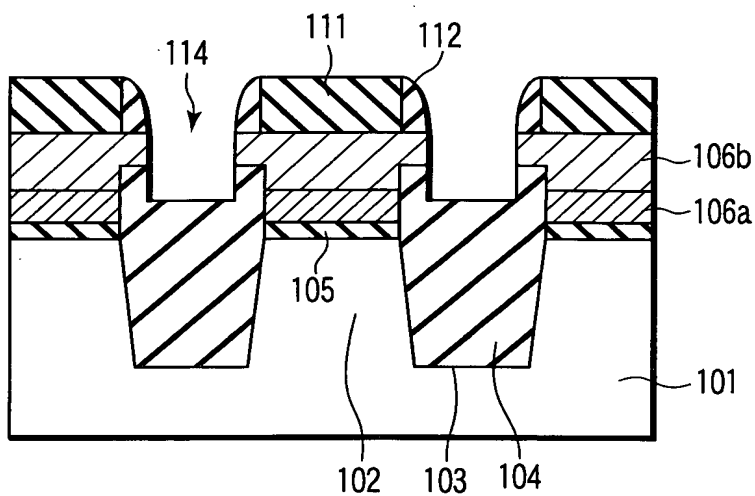


FIG. 15
PRIOR ART

